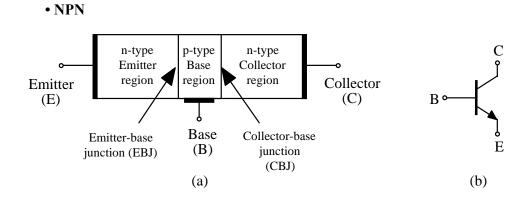
Bipolar Junction Transistors

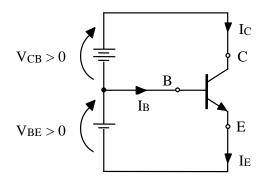
• Physical Structure & Symbols



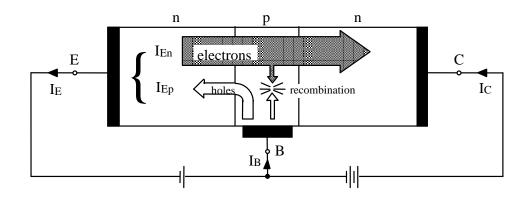
- PNP similar, but:
 - N- and P-type regions interchanged
 - Arrow on symbol reversed
- Operating Modes

Operating mode	EBJ	CBJ
Cut-off	Reverse	Reverse
Active	Forward	Reverse
Saturation	Forward	Forward
Reverse-active	Reverse	Forward

• Active Mode - voltage polarities for NPN



BJT - Operation in Active Mode



+ I_{En} , I_{Ep} both proportional to $exp(V_{BE}/V_T)$

• $I_C \approx I_{En}$

$$\Rightarrow I_C \approx I_S \exp(V_{BE}/V_T) \tag{1.1}$$

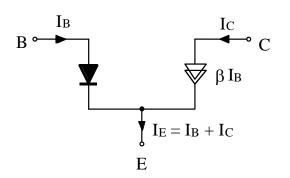
•
$$I_B \approx I_{Ep} \ll I_{En}$$

 \Rightarrow can write $I_C = \beta I_B$ where β large (1.2)

•
$$I_S = SATURATION CURRENT (typ 10^{-15} to 10^{-12} A)$$

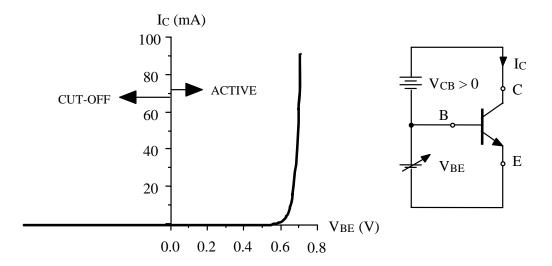
• $V_T = THERMAL VOLTAGE = kT/e \approx 25 mV at 25 °C$
• $\beta = COMMON-EMITTER CURRENT GAIN (typ 50 to 250)$

• Active Mode Circuit Model



BJT Operating Curves - 1





• ACTIVE REGION:

• $I_C \approx 0$ for $V_{BE} < \approx 0.5 V$

- I_C rises very steeply for $V_{BE} > \approx 0.5 V$
- $V_{BE} \approx 0.7$ V over most of useful I_C range

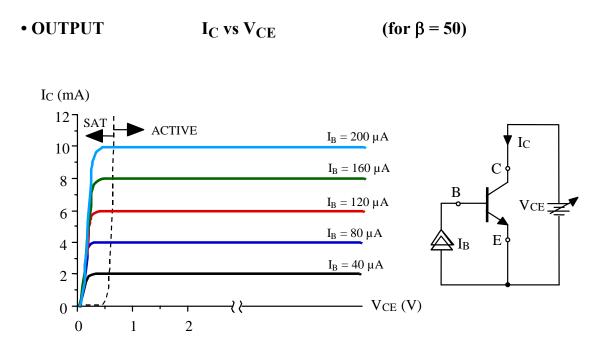
• I_B vs V_{BE} similar, but current reduced by factor β

• CUT-OFF REGION:

• $I_C \approx 0$

• Also I_B , $I_E \approx 0$

BJT Operating Curves - 2



• ACTIVE REGION ($V_{CE} > V_{BE}$):

• I_C = β I_B , regardless of V_{CE}

i.e. CONTROLLED CURRENT SOURCE

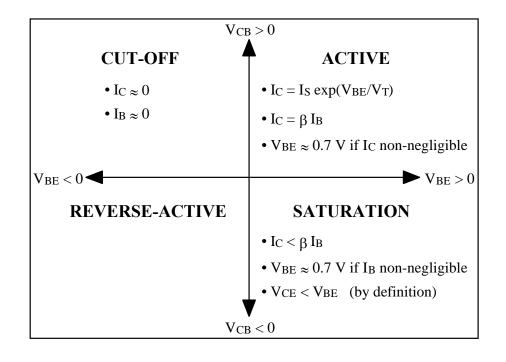
• SATURATION REGION (V_{CE} < V_{BE}):

• I_C falls off as $V_{CE} \rightarrow 0$

• $V_{CEsat} \approx 0.2$ V on steep part of each curve

• In both cases:

• $V_{BE} \approx 0.7 \text{ V}$ if I_B non-negligible



Summary of BJT Characteristics

• Also $I_E = I_B + I_C$ (always)

• THIS TABLE IS IMPORTANT - GET TO KNOW IT !

• For PNP table:

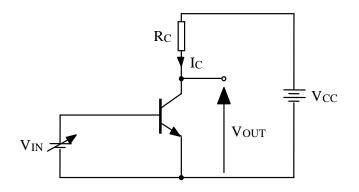
• Reverse order of suffices on all voltages in table

i.e. $V_{CB} \rightarrow V_{BC}$ etc

• Reverse arrows on currents in circuit

i.e. arrows on $I_B,\,I_C$ point out of PNP device, while arrow on I_E points in.

Common-Emitter Amplifier Conceptual Circuit



• Assume active mode:

$$I_C = I_S \exp(V_{IN}/V_T)$$

• Apply Ohm's Law and KVL to output side:

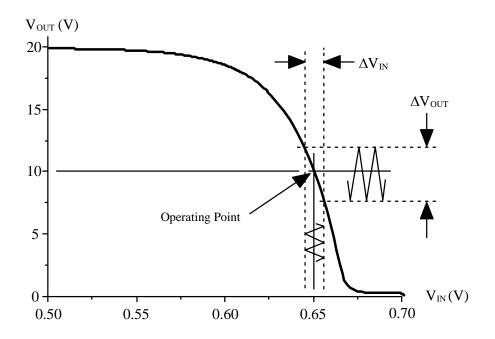
$$\mathbf{V}_{\mathbf{OUT}} = \mathbf{V}_{\mathbf{CC}} - \mathbf{R}_{\mathbf{C}}\mathbf{I}_{\mathbf{C}} \tag{1.3}$$

= $V_{CC} - R_C I_S \exp(V_{IN}/V_T)$

NOTE: Called 'common-emitter' because emitter is connected to reference point for both input and output circuits. Common-Base and Common-Collector also important.

C-E Amplifier Input-Output Relationship

• e.g. $V_{CC} = 20 \text{ V}$, $R_C = 10 \text{ k}\Omega$, $I_S = 10^{-14} \text{ A}$, $V_T = 25 \text{ mV}$.



• Plenty of voltage gain i.e. $\Delta V_{OUT} >> \Delta V_{IN}$

BUT:

- Highly non-linear
 - ⇒ Output distorted unless input signal very small
 - ⇒ Need to BIAS transistor to operate in correct region of graph to get high gain without distortion

C-E Amplifier Small-Signal Response - 1

Aim: to get quantitative information about the small-signal voltage gain and the linearity of a C-E amplifier

• Start with the large signal equations:

$$V_{OUT} = V_{CC} - R_C I_C$$
$$= V_{CC} - R_C I_S \exp(V_{IN}/V_T)$$

• Suppose we add to V_{IN} a small input signal voltage v_{in} , resulting in a corresponding signal v_{out} at the output. We can relate v_{out} to v_{in} by expanding the above as a Taylor series:

$$V_{OUT} + v_{out} = V_{CC} - R_C I_C [1 + v_{in}/V_T + (v_{in}/V_T)^2/2 + ..]$$
 (1.5)

• Assuming $v_{in} \ll V_T$, we can neglect quadratic and higher terms, giving:

$$V_{OUT} + v_{out} \approx V_{CC} - R_C I_C - R_C (I_C/V_T) v_{in} \qquad v_{in} \ll V_T$$

This is a LINEAR APPROXIMATION, valid only when v_{in} is small

Cont'd..

C-E Amplifier Small-Signal Response - 2

- Using (1.3), we can separate the output voltage into BIAS and SIGNAL components:
 - $V_{OUT} = V_{CC} R_C I_C$ Quiescent O/P Voltage

 $v_{out} \approx - R_C (I_C / V_T) v_{in}$ Output Signal

• SMALL-SIGNAL VOLTAGE GAIN:

$$A_v = v_{out}/v_{in} = -R_C I_C / V_T = -R_C g_m$$
 (1.10)

e.g. If quiescent O/P voltage lies roughly mid-way between the supply rails then $R_C I_C \approx V_{CC}$ /2. In this case $A_v = -V_{CC}$ /(2V_T), so for $V_{CC} = 20$ V we get $A_V = -400$.

The quantity $g_m = I_C/V_T$ is known as the TRANSCONDUCTANCE of the transistor.

• LINEARITY

Include higher order terms from Equation 1.5:

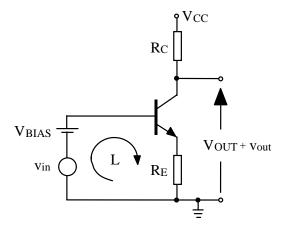
$$v_{out} \approx -R_c g_m [v_{in} + v_{in}^2/2 V_T +]$$

Ratio of unwanted quadratic term to linear term is $v_{in}/2V_T$, so expect 10 % distortion when $v_{in}/2V_T \approx 0.1$, or $v_{in} \approx 5$ mV.

 \Rightarrow Amplifier is linear only for very small signals

Bias Stabilisation - 1

- Biasing at constant V_{BE} is a bad idea, because I_S and V_T both vary with temperature, and we require constant I_C (or I_E) for stable operation. Also, I_S is not a well-defined transistor parameter.
- We can obtain approximately constant I_E as follows:



• KVL in loop L (with no signal) gives:

$$I_E = (V_{BIAS} - V_{BE}) / R_E$$
 (1.11)
 $\approx (V_{BIAS} - 0.7 V) / R_E$ if $V_{BIAS} >> V_{BE}$

 \Rightarrow I_E relatively insensitive to exact value of V_{BE}

• Get I_C from $I_C = \alpha I_E$ where $\alpha = \beta/(1 + \beta) \approx 1$

• a is the COMMON-BASE CURRENT GAIN

Bias Stabilisation - 2

• R_E provides NEGATIVE FEEDBACK

i.e. if the emitter current starts to rise as a result of some change in the transistor's characteristics, then the voltage across R_E rises accordingly. This in turn lowers the base-emitter voltage of the transistor, tending to bring the emitter current back down towards its original value.

⇒ STABILISATION

BUT R_E also:

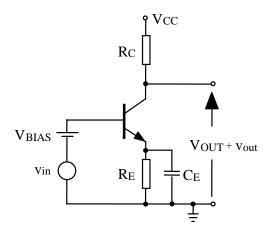
• Reduces small-signal voltage gain:

$$A_{v} = -R_{C} g_{m} / (1 + I_{E}R_{E}/V_{T}) \qquad (1.12)$$
$$\approx -\alpha R_{C}/R_{E}$$

• Reduces output swing

Bias Stabilisation - 3 Recovery of Small-Signal Voltage Gain

• We can recover the original value of A_v for AC signals by using a BYPASS CAPACITOR:



• Now we have:

$$A_v = -R_C g_m /(1 + I_E Z_E / V_T)$$
 (1.12b)

where Z_E is the combined impedance of R_E and C_E :

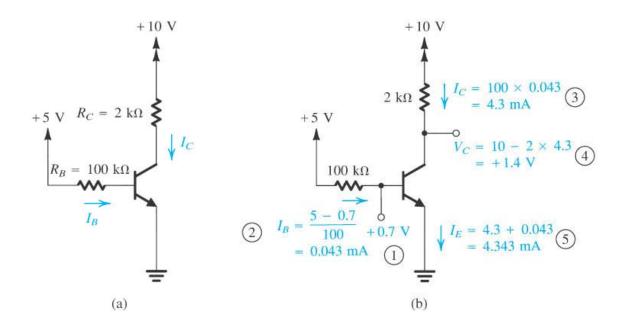
$$Z_E = R_E / (1 + j \omega R_E C_E)$$

By making C_E large enough, we can make the parallel combination appear like a short circuit (i.e. $|Z_E| \approx 0$) at all AC frequencies of interest, so that Equation 1.12b reduces to $A_v \approx - R_C g_m$ as for our original common-emitter amplifier. On the other hand, the capacitor has no effect on biasing, because it passes no DC current.

NB Technique only really relevant to discrete circuits (no big capacitors inside IC's!)

Example 1

Analyze the circuit below to determine the voltages at all nodes and the currents in all branches. Assume $\beta = 100$.



1. V_{BE} is around 0.7V

$$I_{B} = \frac{+5 - V_{BE}}{R_{B}} \approx \frac{5 - 0.7}{100} = 0.043 \text{ mA}$$
2.

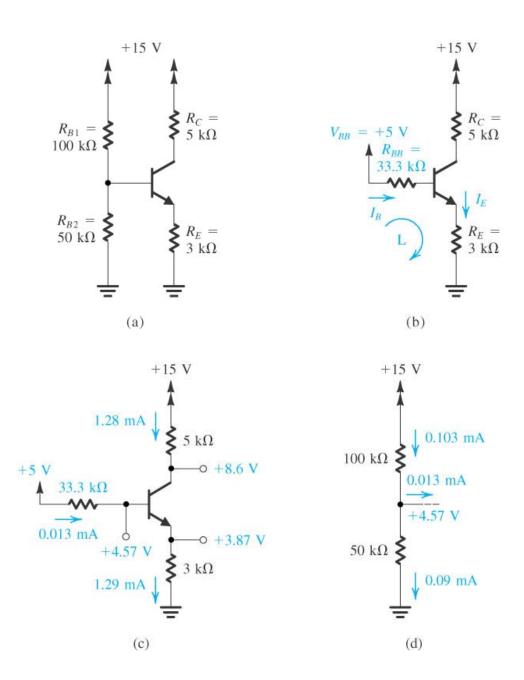
$$I_{C} = \beta I_{B} = 100 \times 0.043 = 4.3 \text{ mA}$$
3.

$$V_{C} = +10 - I_{C}R_{C} = 10 - 4.3 \times 2 = +1.4 \text{ V}$$
5.

$$I_{E} = (\beta + 1)I_{B} = 101 \times 0.043 = 4.3 \text{ mA}$$

Example 2

Analyze the circuit below to determine the voltages at all nodes and the currents in all branches. Assume $\beta = 100$.



Step 1: Simplify base circuit using Thévenin's theorem.

$$V_{BB} = +15 \frac{R_{B2}}{R_{B1} + R_{B2}} = 15 \frac{50}{100 + 50} = +5 \text{ V}$$
$$R_{BB} = (R_{B1} // R_{B2}) = (100 // 50) = 33.3 \text{ k}\Omega$$

Step 2: Evaluate the base or emitter current by writing a loop equation around the loop marked L.

$$V_{BB} = I_B R_{BB} + V_{BE} + I_E R_E$$

Substituting for I_B by

.

$$I_B = \frac{I_E}{\beta + 1}$$

and rearranging the equation gives

$$I_{E} = \frac{V_{BB} - V_{BE}}{R_{E} + [R_{BB}/(\beta + 1)]}$$

For the numerical values given we have

$$I_E = \frac{5 - 0.7}{3 + (33.3/101)} = 1.29 \text{ mA}$$

The base current will be

$$I_B = \frac{1.29}{101} = 0.0128 \text{ mA}$$

• Step 3: Now evaluate all the voltages.

$$V_B = V_{BE} + I_E R_E = 0.7 + 1.29 \times 3 = 4.57V$$
$$I_C = (\frac{\beta}{1+\beta})I_E = 0.99 \times 1.29 = 1.28mA$$

$$V_c = +15 - I_c R_c = 15 - 1.28 \times 5 = 8.6V$$